

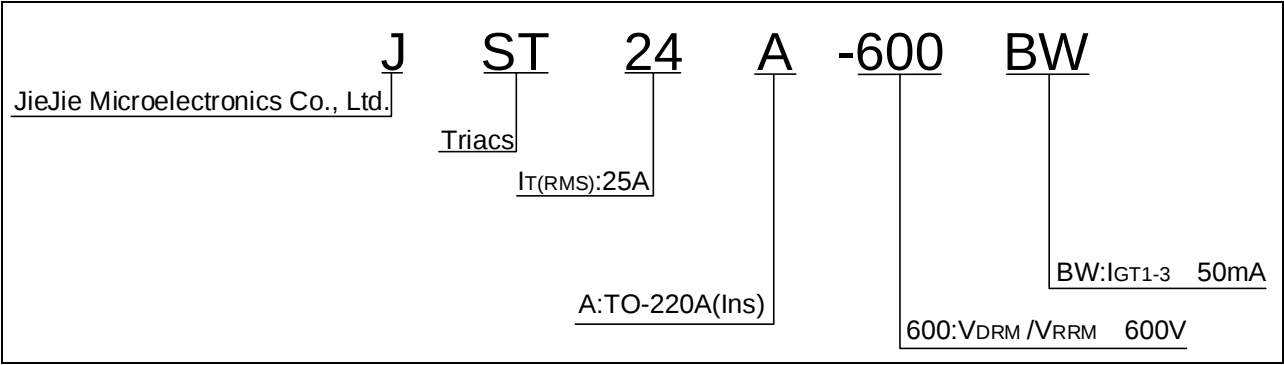
JST24A-600BW

Average gate power dissipation
Peak gate power
Peak pulse voltage (T _j =25 ; non-repetitive, off-state)

ELECTRICAL CHARACTERISTICS

Symbol	Test Condition
I _{GT}	V _D =12V R _L =33
V _{GT}	
V _{GD}	V _D =V _{DRM} T _j =125 R _L =3.3k
I _L	I _G =1.2I _{GT}

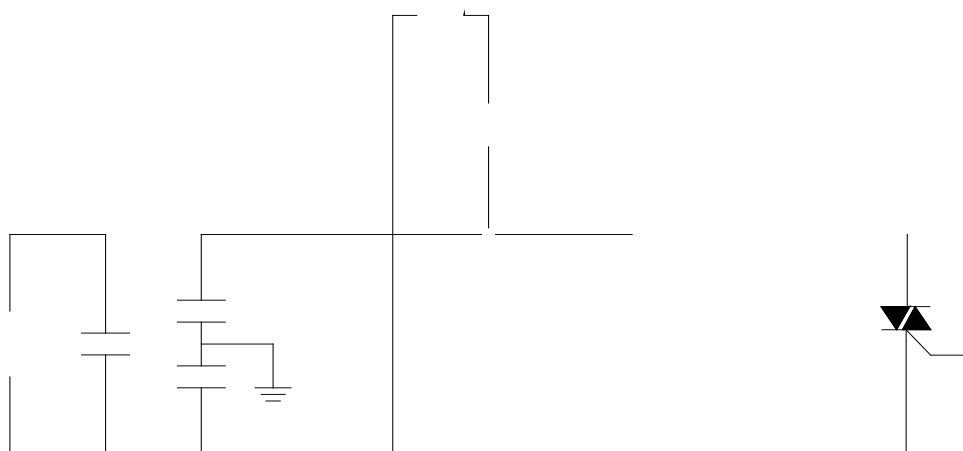
ORDERING INFORMATION



MARKING



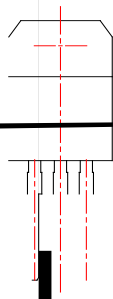
FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



JST24A-600BV

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PACKAGE MECHANICAL DATA



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